DEC 1 5 2004 15

MW

Nicole Barrese Accoll Bowene 12/13/04

Name of Person Making Deposit With United States Postal Service	e Signature of Person Making Deposit
IN THE UNITED STATES PATE	NT AND TRADEMARK OFFICE
In re application of: Huilong Zhu, et al.	Date: December 13, 2004
Serial Number: 10/709,239	Examiner:
Filed: 4/23/2004	Group Art Unit: 2811
Title: STRUCTURES AND METHODS FOR MANUFACTURING OF DISLOCATION FREE STRESSED CHANNELS IN BULK SILICON AND SOI CMOS DEVICES BY GATE STRESS ENGINEERING WITH SIGE AND/OR SI:C	IBM Corporation D/18G, B/300, Zip 482 2070 Route 52 Hopewell Junction, NY 12533-6531

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

Huilong Zhu, et al.

Joseph P. Abate

Registration No. 30,238

Telephone: (845) 894-4633

FIS920030375

		$-\sqrt{01}$				1		
FORM PTO-	1449 (Modified)	(DEC,	` ,	ATTY. DOCKET NO F1S920030375	•	SERIAL NO 10/709,		
LIST OF PATAPPLICANT	TENTS AND PUBLICA 'S INFORMATION DIS	TIONS FOR 5	2004	ADDI ICANIT:	.41			
STATEMEN		S. S. Jesus	OFF		-	Zhu, et a	al.	
(Use several s	heets if necessary)			FILING DATE: 4/23	GROUP: 2811			
REFERENCE I	DESIGNATION	U.S.	PATE	NT DOCUMENTS				
EXAMINER INITIALS	DOCUMENT NUMBER	DATE		NAME		SUBCLAS	•	IG DA
	6,228,694 B1	5/8/2001		Doyle et al.				
	6,406,973 B1	6/18/2002		Lee				
	6,281,532 B1	8/28/2001		Doyle et al.				
	5,683,934	11/4/97		Candelaria				•
	6,368,931 B1	4/9/2002		Kuhn, et al.				_
	5,310,446	5/10/94		Konishi et al.				
	4,853,076	8/1/89		Tsaur et al.				
	UŚ 2002/0090791 A1	7/11/2002		Doyle et al.			·	
	US 2002/0074598 A1	6/20/2002		Doyle et al.				
	6,509,618 B2	1/21/2003		Jan et al.				
	6,476,462 B2	11/5/2002		Shimizu et al.				
	6,362,082 B1	3/26/2002		Doyle et al.				
	6,228,694 B1	5/8/2001		Doyle et al.				
	5,565,697	10/15/96		Asakawa et al.				
	US 2003/0040158 A1	2/27/2003		Saitoh				
	US 2002/0086472 A1	7/4/2002		Roberds et al.				
	6,521,964 B1	2/18/2003		Jan et al.				
	6,506,652	01/14/03		Jan, et al.				
		FOREIG	N PAT	ENT DOCUMENTS				
	DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	TRANSL	l
			···		<u> </u>	1	YES	NO
	OTHER.	ART (Including	g Autho	or, Title, Date, Pertinen	t Pages, etc.			
XAMINER				DATE CONSIDERE	D			··
CAMINER: In	itial if reference consider ce and not considered. I	red, whether or a	not cita his form	tion is in conformance we n with next communicati	rith MPEP 60	09. Draw line	through c	itation

FORM PTO-14	149 (Modified) ENTS AND PUBLIC.	ATIONS FOR	ì	ATTY. DOCKET NO. -FIS920030375			SERIAL NO. 10/709,239		
	INFORMATION DI		APPLICANT: Huil	APPLICANT: Huilong Zhu, et al.					
(Use several she	eets if necessary)		FILING DATE: 4/2	FILING DATE: 4/23/04					
REFERENCE D	ESIGNATION	U.S. 1	PATENT DOCUMENTS	ENT DOCUMENTS					
EXAMINER INITIALS	NITIALS NUMBER		NAME	CLASS	SUBCLAS		NG DAT		
	5,081,513	1/14/1992	Jackson, et al.						
	3,602,841	8/31/1971	McGroddy			1			
	6,531,740	3/11/2003	Bosco, et al.			┧			
	6,531,369	3/11/2003	Ozkan, et al.			┪			
ľ	6,501,121	12/31/2002	Yu, et al.	1	 -	 			
	6,498,358	12/24/2002	Lach, et al.			 			
	6,493,497	12/10/2002	Ramdani, et al.	-		┪—			
	6,403,975	6/11/2002	Brunner, et al.	 	 				
6,361,885 6,255,169	3/26/2002 7/3/2001	Chou	1		 				
		Li, et al.	 		-				
	6,246,095	6/12/2001	Brady, et al.	 		†			
	6,165,383	12/26/2000	Chou	1		 			
	6,133,071	10/17/2000	Nagai	 		 			
	6,046,464	4/4/2000	Schetzina	1	 	 			
	6,025,280	2/15/2000	Brady, et al.		·	1			
		FOREIGN	PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSI YES	LATION		
	OTHER	ART (Including	Author, Title, Date, Pertine	nt Pages, etc	<u>'</u>	 			
		:							
XAMINER			DATE CONSIDERE	D	- 		<u></u>		
XAMINER: Inition of in conformance	ial if reference considered.	ered, whether or no Include copy of th	ot citation is in conformance vis form with next communicate	vith MPEP 60	9. Draw line	through c	itation i		

	FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR			ATTY. DOCKET NO. FIS920030375			SERIAL NO. 10/709,239			
	S INFORMATION DI		APPLICANT:	nullong zhu, et al.						
(Use several sh	neets if necessary)	·	FILING DATE: 4/	FILING DATE: 4/23/04						
REFERENCE D	ESIGNATION	U.S.	PATENT DOCUMENTS							
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLAS		IG DATI			
	5,940,736	8/17/1999	Brady, et al.			7	<u>u 11.0.,</u>			
	5,880,040	3/9/1999	Sun, et al.		1	1				
	5,861,651	1/19/1999	Brasen, et al.			+				
<u> </u>	5,679,965	10/21/1997	Schetzina			- 				
	5,670,798	9/23/1997	Schetzina			+				
	5,561,302	10/1/1996	Candelaria			 				
	5,471,948	12/5/1995	Burroughes, et al.		 	+				
	5,459,346	10/17/1995	Asakawa, et al.	- 	 	+				
5,391,510 5,371,399	2/21/1995	Hsu, et al.			+	·				
	12/6/1994	Burroughes, et al.			 					
	5,108,843	4/28/1992	Ohtaka, et al.	 		 				
	5,060,030	10/22/1991	Hoke	- 		 				
	4,958,213	9/18/1990	Eklund, et al.		-	 				
	4,665,415	5/12/1987	Esaki, et al.	-	-	 				
	6,635,506	10/21/2003	Volant et al.		 	 				
		FOREIG	N PATENT DOCUMENTS			4				
	DOCUMENT			7		TRANSL	ATION			
	NUMBER DATE		COUNTRY	CLASS	SUBCLASS	YES	NO			
	OTHER	ART (Including	Author, Title, Date, Pertine	nt Pages, etc	`		2.0			
	T		, rization, ride, Date, relation	at I ages, etc	·)					
XAMINER			DATE CONSIDERE	D						
XAMINER: Inited to the conformance of the conforman	ial if reference considered.	ered, whether or n Include copy of th	ot citation is in conformance value form with next communication	with MPEP 60	Draw line t	hrough c	itation if			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-14	49 (Modified)		ATTY. DOCKET NO. FIS920030375				SERIAL NO. 10/709,239		
	INTS AND PUBLICA INFORMATION DI		APPLICANT: Huil	APPLICANT: Huilong Zhu, et al.					
(Use several she	eets if necessary)		FILING DATE: 4/	FILING DATE: 4/23/04 GROUP: 2811					
REFERENCE DI	ESIGNATION	U.S.	PATENT DOCUMENTS						
EXAMINER	DOCUMENT						G DATE		
INITIALS	NUMBER	DATE	NAME	CLAS	S SUBCLAS	S (IF A)	PPRO.)		
	5,557,122	9/17/1996	Shrivastava, et al.						
	5,354,695	10/11/1994	Leedy			- 			
	5,134,085	7/28/1992	Gilgen, et al.	-		-			
	5,006,913	4/9/1991	Sugahara, et al.			<u> </u>			
	4,952,524	8/28/1990	Lee, et al.			<u> </u>			
	4,855,245	8/8/1989	Neppl, et al.			-			
	2002/0086497	07-04-2002	Kwok			ļ			
	5,960,297	09-28-1999	Saki						
	6,403,486	06-11-2002	Lou						
	6,284,623	09-04-2001	Zhang et al.			<u> </u>			
	2003/0032261	02-13-2003	Yeh et al.						
, ,	2003/0057184	03-27-2003	Yu et al.			J			
	6,265,317	07-24-2001	Chiu et al.	<u> </u>					
	2003/0067035	04-10-2003	Tews et al.						
	6,461,936	10-08-2002	von Ehrenwall						
	6,319,794	11-20-2001	Akatsu et al.						
	2001/0009784	07-26-2001	Ma et al.						
	6,621,392	09-16-2003	Volant et al.						
		FOREIG	EN PATENT DOCUMENTS						
	DOCUMENT					TRANSL	ATION		
	NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO		
	ОТНЕ	R ART (Includin	g Author, Title, Date, Pertiner	it Pages, et	c.)				
					· ·				
EXAMINER			DATE CONSIDERE	D					
			not citation is in conformance v this form with next communicat			through c	itation i		

FORM PTO-1449 (Modified)
LIST OF PATENTS AND PUBLICATIONS
FOR APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Docket Number (Optional)	Application Number				
FIS920030375	10/709,239				
Applicant(s) Huilong Zhu, et al.					
Filing Date	Group Art Unit				
4/23/04	2811				

					4/23/04			2811	
		-		U.S. PATENT DOCUM	IENTS				
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS		NG DATE
		5,940,716	8/17/1999	Jin, et al.					NOT REAL CO.
					·				
							-		
									· · · · · · · · · · · · · · · · · · ·
				FOREIGN PATENT DO	CUMENTS				
	REF	DOCUMENT NUMBER	DATE	COUNTRY		CLASS SUB	SUBCLASS	Trans YES	station NO
								T Los	, RO
	\Box				·				
			: :	OTHER DOCUMENTS	(Including A	uthor, Title, Dat	te, Pertinent Pag	zes, Etc.)	
									
		·							
;		·							

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

DATE CONSIDERED

EXAMINER

							raye	= •	
	FORM PTO-1449 (Mo	-		ATTY. DOCKET NO. FIS92003037	5	SERIAL NO.			
	ENTS AND PUBLICA S INFORMATION DIS		4	APPLICANT: Huilong Zhu, et al.					
(Use several sh	eets if necessary)]	FILING DATE: 4/23/04 GROUP: 2811					
REFERENCE D	ESIGNATION	U.S. PA	TEN	T DOCUMENTS					
EXAMINER INITIALS				NAME	CLASS	SUBCLAS		G DATE PPRO.)	
				:					
		FOREIGN	TO 4 071				<u></u>		
· · · · · · · · · · · · · · · · · · ·		FUREIGN	PATI	ENT DOCUMENTS	<u> </u>				
	DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	TRANS	NO	
	OTHER	ART (Including A	Lutho	r, Title, Date, Pertinent	Pages, etc	L)			
	Kern Rim, et al., * International Elec	Transconductance tron Devices Meet	e Ent	nancement in Deep Su 26, 8, 1, IEEE, Septem	bmicron S ber 1998.	Strained-Si n-I	MOSFET	s",	
	Kern Rim, et al.,	Characteristics an	d De	vice Design of Sub-10 Digest of Technical Pa	0 nm Stra	ined Si N- an	PMOS	FETs",	
	Gregory Scott, et Isolation Induced	al., "NMOS Drive Stress", Internatio	Cume nal E	ent Reduction Caused lectron Devices Meeti	by Transi ng, 34.4.1	stor Layout ar , IEEE, Septe	d Trenc mber 19	h 99.	
				-Performance 130nm ernational Electron De					
				s Effect of Etch-Stop Nitride and its Impact on Deep Submicron ectron Devices Meeting, 10.7.1, IEEE, April 2000.					
	Enhancement, In	ternational Electro	n De	ess Control (LMC): A N vices Meeting, IEEE, I	March 200)1			
	K. Ota, et al., "No International Elec	vel Locally Straine fron Devices Meet	d Chaing, 2	annel Technique for hi .2.1, IEEE, February 2	gh Perfon 2002.	mance 55nm	CMOS",		
EXAMINER				DATE CONSIDERED					
				1				1	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.